

Silicon NPN Power Transistors

2SC3893

DESCRIPTION

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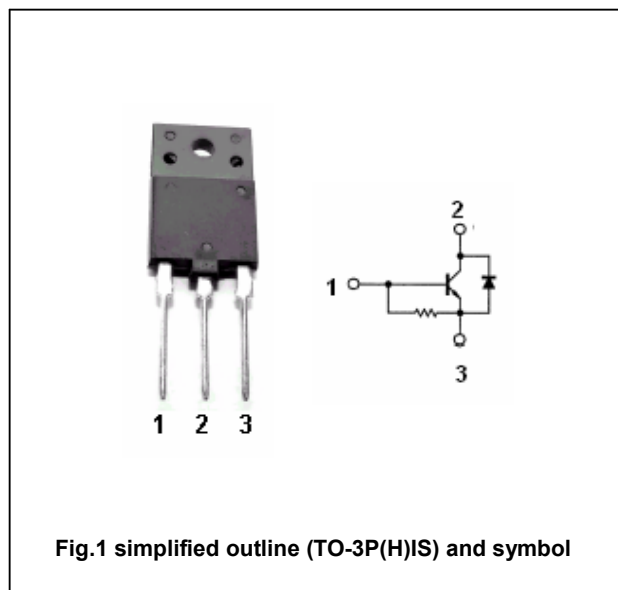
- With TO-3P(H)IS package
- Built-in damper diode
- High voltage ,high speed

APPLICATIONS

- Horizontal deflection output for high resolution display

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1400	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		15	A
I_B	Base current		4	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

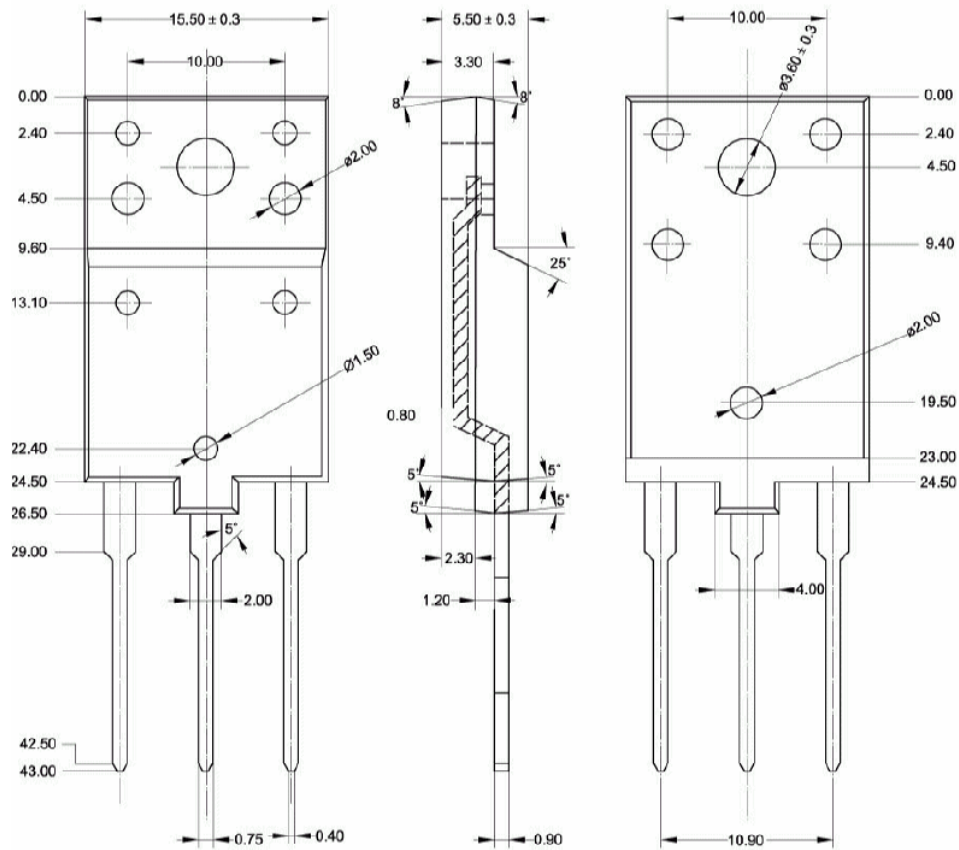
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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=200mA, I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=6A; I_B=1.5A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=6A; I_B=1.5A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=500V; I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$	66		200	mA
h_{FE}	DC current gain	$I_C=1A; V_{CE}=5V$	8	12		
f_T	Transition frequency	$I_C=0.1A; V_{CE}=10V$	1	3		MHz
C_{OB}	Collector output capacitance	$I_E=0; V_{CB}=10V; f=1MHz$		210		pF
V_F	Diode forward voltage	$I_F=6A$			2.0	V
t_s	Storage time	Resistive load $I_{CP}=6A; I_{B1}=1.2A; I_{B2}=-2.4A$ $R_L=33.3\Omega$			2.5	μs
t_f	Fall time				0.2	μs

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PACKAGE OUTLINE

www.datasheet4u.comFig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)